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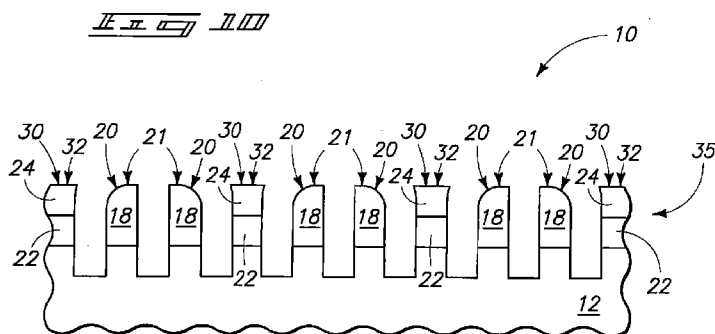
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(54) Title: METHODS OF FABRICATING SUBSTRATES



(57) Abstract: A method of fabricating a substrate includes forming first and second spaced features over a substrate. The first spaced features have elevationally outermost regions which are different in composition from elevationally outermost regions of the second spaced features. The first and second spaced features alternate with one another. Every other first feature is removed from the substrate and pairs of immediately adjacent second features are formed which alternate with individual of remaining of the first features. After such act of removing, the substrate is processed through a mask pattern comprising the pairs of immediately adjacent second features which alternate with individual of the remaining of the first features. Other embodiments are disclosed.